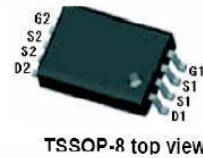
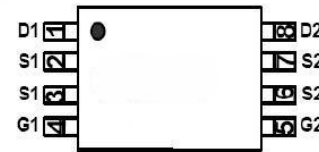
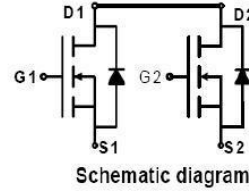


Features

For a single MOSFET
 $V_{DSS} = 20\text{ V}$
 $R_{DS(ON)} = 21\text{ m}\Omega @ V_{GS} = 4.5$

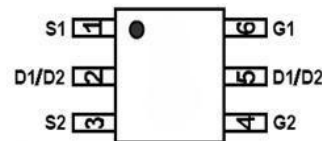


Applications

- Battery protection
- Load switch
- Power management

Construction

- Silicon epitaxial planer

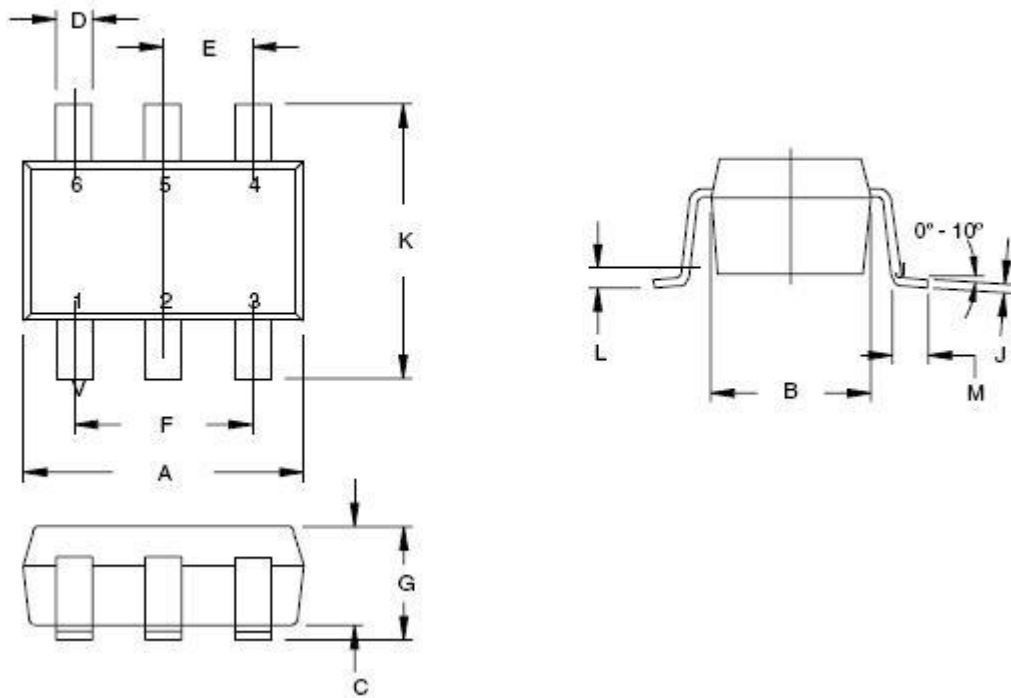


Absolute Maximum Ratings

Paramet		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	20	V
Gate-Source Voltage		V_{GS}	± 10	V
Drain Current (Note 1)	Continuous	I_D	6	A
	Pulsed	I_{DM}	25	
Maximum Power Dissipation		P_D	1.5	W
Operating Junction Temperature Range		T_J	-55 to 150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}		

SE8205

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
B _{VDSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0 V			1	μA
I _{GSS}	Gate-Body leakage	V _{DS} =0V, V _{GS} =±12 V			±80	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.45	0.6	1.2	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =4.0V, I _D =6.8A	-	21	24.5	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A	3			S
DYNAMIC						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =8V, f=1.0MHz		600		pF
C _{oss}	Output Capacitance			330		pF
C _{rss}	Reverse Transfer Capacitance			140		pF
SWITCHING						
Q _g	Total Gate Charge	V _{GS} =4.5V V _{DS} =10V I _D =6A		10	15	nC
Q _{gs}	Gate Source Charge			2.3		
Q _{gd}	Gate Drain Charge			3		
t _{d(on)}	Turn-On DelayTime	V _{GEN} =4.0V R _{GEN} =10Ω V _{DD} =10V I _D =1A		10	20	ns
t _{d(off)}	Turn-Off DelayTime			35	70	
t _{d(r)}	Turn-On Rise Time			11	25	
t _{d(f)}	Turn-Off Fall Time			30	60	



PACKAGE DIMENSIONS				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.90	3.00	0.114	0.118
B	1.50	1.75	0.059	0.070
C	0.90	1.30	0.036	0.051
D	0.35	0.50	0.014	0.020
E	0.85	1.05	0.033	0.040
F	1.70	2.10	0.067	0.083
G	0.90	1.45	0.036	0.057
J	0.090	0.20	0.0035	0.008
L	0.20TYP	0.20TYP	0.007TYP	0.007TYP
K	2.72	2.88	0.107	0.113
M	0.35	0.55	0.014	0.022

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